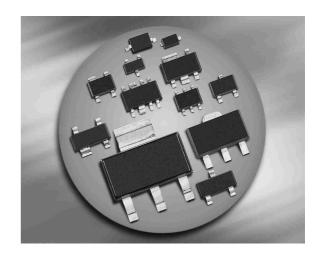


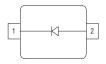
Silicon Variable Capacitance Diodes

- Frequency range up to 2 GHz
- Special design for use in TV-sat tuners
- Pb-free (RoHS compliant) package





BB831



Туре	Package	Configuration	L S(nH)	Marking
BB831	SOD323	single	1.8	white T

Maximum Ratings at T_A = 25°C, unless otherwise specified

Parameter	Symbol	Value	Unit	
Diode reverse voltage	V_{R}	30	V	
Peak reverse voltage	V_{RM}	35		
$(R \ge 5k\Omega)$				
Forward current	I _F	20	mA	
Operating temperature range	T_{op}	-55 125	°C	
Storage temperature	$T_{ m stg}$	-55 150		

1 2011-06-15



Electrical Characteristics at $T_A = 25$ °C, unless otherwise specified

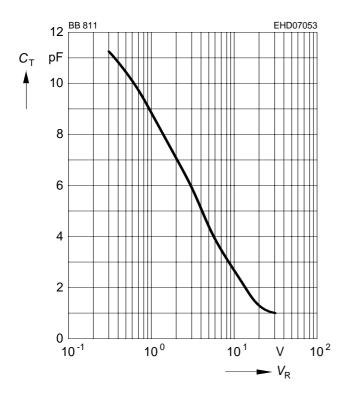
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Reverse current	I_{R}				nA
<i>V</i> _R = 30 V		-	-	20	
V_{R} = 30 V, T_{A} = 85 °C		-	-	500	
AC Characteristics					
Diode capacitance	C_{T}				pF
$V_{R} = 1 \text{ V}, f = 1 \text{ MHz}$		7.8	8.8	9.8	
$V_{R} = 28 \text{ V}, f = 1 \text{ MHz}$		0.85	1.02	1.2	
Capacitance ratio	C _{T1} /C _{T28}	7.8	8.6	9.5	
$V_{R} = 1 \text{ V}, V_{R} = 28 \text{ V}, f = 1 \text{ MHz}$					
Capacitance matching ¹⁾	$\Delta C_{T}/C_{T}$	-	-	3	%
V_{R} = 1 V, V_{R} = 28 V, f = 1 MHz					
Series resistance	$r_{\mathbb{S}}$	_	1	-	Ω
$V_{R} = 1 \text{ V}, f = 100 \text{ MHz}$					

2

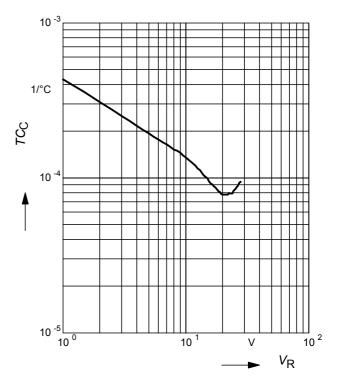
¹For details please refer to Application Note 047.



Diode capacitance $C_T = f(V_R)$ f = 1MHz



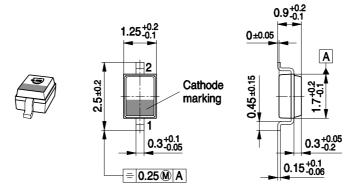
Temperature coefficient of the diode capacitance $T_{Cc} = f(V_R)$



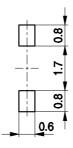
3 2011-06-15



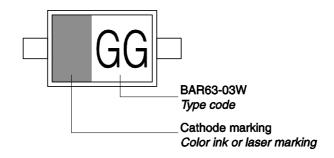
Package Outline



Foot Print

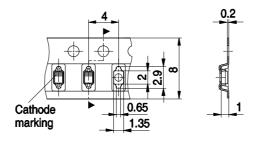


Marking Layout (Example)



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel Reel ø330 mm = 10.000 Pieces/Reel



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Edition 2009-11-16

Published by Infineon Technologies AG 81726 Munich, Germany

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